

Excellent Integrated System Limited

Stocking Distributor

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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-MBR1035-N3</u>

For any questions, you can email us directly: sales@integrated-circuit.com

VISHA

Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite

Datasheet of VS-MBR1035-N3 - DIODE SCHOTTKY 35V 10A TO220AC

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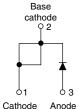


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Vishay Semiconductors

Schottky Rectifier, 10 A





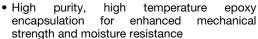
TO	-220	1

Bas	e
catho	ode
Υ	2
1	
•	—
01	0.3
01	0.0
Cathode	Anode

PRODUCT SUMMARY	•
Package	TO-220AC
I _{F(AV)}	10 A
V_{R}	35 V, 45 V
V _F at I _F	0.57 V
I _{RM} max.	15 mA at 125 °C
T _J max.	150 °C
Diode variation	Single die
E _{AS}	8 mJ

FEATURES

- 150 °C T_J operation
- High frequency operation
- · Low forward voltage drop





- Guard ring for enhanced ruggedness and long term reliability
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)

DESCRIPTION

This Schottky rectifier has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 150 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS								
SYMBOL	CHARACTERISTICS	CHARACTERISTICS VALUES UNITS						
I _{F(AV)}	Rectangular waveform	10	Δ.					
I _{FRM}	T _C = 135 °C	20	A					
V _{RRM}		35/45	V					
I _{FSM}	t _p = 5 µs sine	1060	А					
V _F	10 A _{pk} , T _J = 125 °C	0.57	V					
T _J	Range	- 65 to 150	°C					

VOLTAGE RATINGS									
PARAMETER	SYMBOL	VS-MBR1035PbF	VS-MBR1035-N3	VS-MBR1045PbF	VS-MBR1045-N3	UNITS			
Maximum DC reverse voltage	V_{R}	35	35	45	45	V			
Maximum working peak reverse voltage	V _{RWM}	ან	ან	45	45	V			

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST	TEST CONDITIONS		UNITS		
Maximum average forward current	I _{F(AV)}	T_C = 135 °C, rated V_R	T _C = 135 °C, rated V _R		Α		
Peak repetitive forward current	I _{FRM}	Rated V _R , square wave, 20	Rated V _R , square wave, 20 kHz, T _C = 135 °C		^		
Non-repetitive peak surge current	I _{ESM}	5 μs sine or 3 μs rect. pulse	Following any rated load condition and with rated V _{RRM} applied	1060	А		
, , ,	1 0101	Surge applied at rated load conditions halfwave, single phase, 60 Hz		150			
Non-repetitive avalanche energy	E _{AS}	$T_J = 25 ^{\circ}\text{C}$, $I_{AS} = 2 \text{A}$, $L = 4 \text{mH}$		8	mJ		
Repetitive avalanche current	I _{AR}	Current decaying linearly to zero in 1 μ s Frequency limited by T_J maximum $V_A=1.5$ x V_R typical		2	А		

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VS-MBR10...PbF Series, VS-MBR10...-N3 Series

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ELECTRICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS	
		20 A	T _J = 25 °C	0.84		
Maximum forward voltage drop	V _{FM} ⁽¹⁾	10 A	T. 105 °C	0.57	V	
		20 A	- T _J = 125 °C	0.72		
Mariana	I _{RM} ⁽¹⁾	T _J = 25 °C	Rated DC voltage	0.1	- mA	
Maximum instantaneous reverse current		T _J = 125 °C		15		
Threshold voltage	V _{F(TO)}	T T mayimum		0.354	V	
Forward slope resistance	r _t	$T_J = T_J$ maximum		17.6	mΩ	
Maximum junction capacitance	C _T	$V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHz) 25 °C		600	pF	
Typical series inductance	L _S	Measured from top of terminal to mounting plane		8.0	nH	
Maximum voltage rate of change	dV/dt	Rated V _R		10 000	V/µs	

Note

 $^{^{(1)}\,}$ Pulse width < 300 µs, duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction temperature range	TJ		- 65 to 150	°C		
Maximum storage temperature range	T _{Stg}		- 65 to 175	*U		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	2.0	°C/W		
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth and greased (only for TO-220)	0.50	O/VV		
Approximate weight			2	g		
Approximate weight			0.07	OZ.		
Mounting to roug	1		6 (5)	kgf · cm		
Mounting torque — maximum	ī		12 (10)	(lbf · in)		
Marking device		Case style TO-220AC	MBR	1035		
warking device		Case style 10-220AC	MBR	1045		

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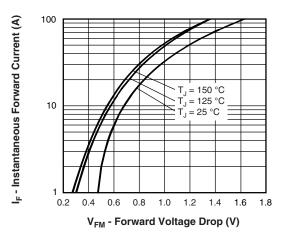


Fig. 1 - Maximum Forward Voltage Drop Characteristics

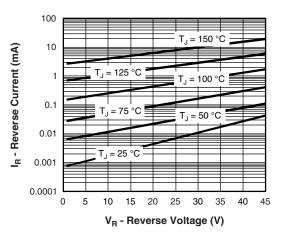


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

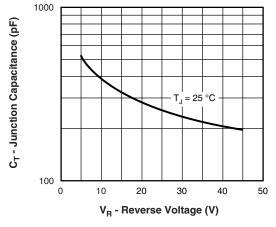


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

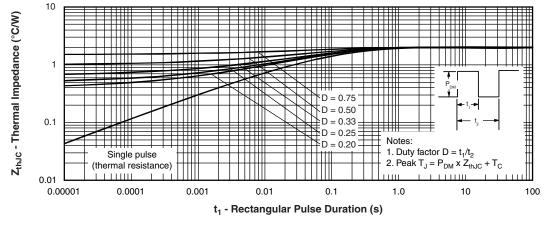


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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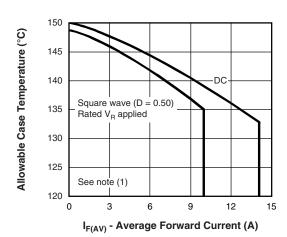


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

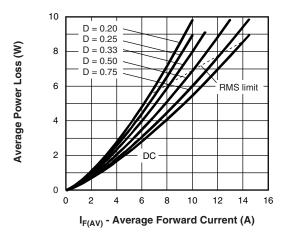


Fig. 6 - Forward Power Loss Characteristics

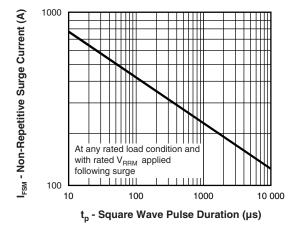


Fig. 7 - Maximum Non-Repetitive Surge Current

Note

 $^{(1)}$ Formula used: $T_C = T_J$ - (Pd + Pd_{REV}) x R_{thJC}; Pd = Forward power loss = $I_{F(AV)}$ x V_{FM} at ($I_{F(AV)}$ /D) (see fig. 6); Pd_{REV} = Inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = Rated V_R

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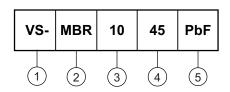




Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - Schottky MBR series

- Currrent rating (10 = 10 A)

- Voltage ratings — 35 = 35 V 45 = 45 V

5 - Environmental digit

• PbF = Lead (Pb)-free and RoHS compliant

• -N3 = Halogen-free, RoHS compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-MBR1035PbF	50	1000	Antistatic plastic tube				
VS-MBR1035-N3	50	1000	Antistatic plastic tube				
VS-MBR1045PbF	50	1000	Antistatic plastic tube				
VS-MBR1045-N3	50	1000	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95221</u>				
Doub an ordinary information	TO-220AC PbF	www.vishay.com/doc?95224		
Part marking information	TO-220AC -N3	www.vishay.com/doc?95068		
SPICE model		www.vishay.com/doc?95293		

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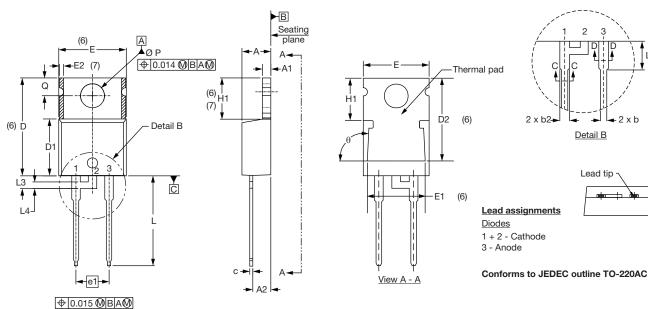


Outline Dimensions

Vishay Semiconductors

TO-220AC

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
E	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
L3	1.78	2.13	0.070	0.084	
L4	0.76	1.27	0.030	0.050	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° t	o 93°	

Notes

- $^{(1)}\,$ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- $^{(7)}$ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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